

# Mohammad Wahidur Rahman

## List of Publications by Year in descending order

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9  
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#	ARTICLE	IF	CITATIONS
1	Demonstration of BaTiO <sub>3</sub> Integrated kV-class AlGa <sub>N</sub> /Ga <sub>N</sub> Schottky Barrier Diodes with Record Average Breakdown Electric Field. , 2022, , .		0
2	Hybrid BaTiO <sub>3</sub> /SiN <sub>x</sub> /AlGa <sub>N</sub> /Ga <sub>N</sub> lateral Schottky barrier diodes with low turn-on and high breakdown performance. Applied Physics Letters, 2021, 119, 013504.	3.3	6
3	Breakdown Voltage Enhancement in ScAlN/GaN High-Electron-Mobility Transistors by High- <i>k</i> Bismuth Zinc Niobate Oxide. IEEE Transactions on Electron Devices, 2021, 68, 3333-3338.	3.0	14
4	Integration of high permittivity BaTiO <sub>3</sub> with AlGa <sub>N</sub> /Ga <sub>N</sub> for near-theoretical breakdown field kV-class transistors. Applied Physics Letters, 2021, 119, .	3.3	11
5	Linearity Improvement With AlGa <sub>N</sub> Polarization- Graded Field Effect Transistors With Low Pressure Chemical Vapor Deposition Grown SiN <sub>x</sub> Passivation. IEEE Electron Device Letters, 2020, 41, 19-22.	3.9	36
6	Design and Fabrication of Vertical Ga <sub>N</sub> p-n Diode With Step-Etched Triple-Zone Junction Termination Extension. IEEE Transactions on Electron Devices, 2020, 67, 3553-3557.	3.0	17
7	High-permittivity dielectric edge termination for vertical high voltage devices. Journal of Computational Electronics, 2020, 19, 1538-1545.	2.5	7
8	Local electric field measurement in Ga <sub>N</sub> diodes by exciton Franz-Keldysh photocurrent spectroscopy. Applied Physics Letters, 2020, 116, .	3.3	2
9	BaTiO <sub>3</sub> /Al <sub>0.58</sub> Ga <sub>0.42</sub> N lateral heterojunction diodes with breakdown field exceeding 8 MV/cm. Applied Physics Letters, 2020, 116, .	3.3	17